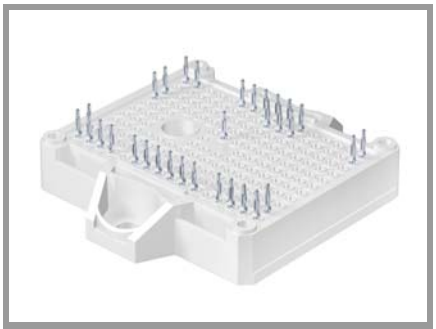
SK50DGDL066ETE2



SEMITOP®E2

3-phase bridge rectifer + brake chopper + 3-phase bridge inverter

Engineering Sample

SK50DGDL066ETE2

Target Data

Features*

- Low inductive design
- Press-Fit contact technology
- Rugged mounting due to integrated mounting clamps
- Heat transfer and insulation through direct copper bonded aluminium oxide ceramic (DBC)
- Trench IGBT3 technology
- Robust and soft switching CAL4F diode technology
- Integrated NTC temperature sensor
- UL recognized file no. E 63 532

Typical Applications

- Motor drives
- Air conditioning
- Auxiliary Inverters

Remarks

- IGBT1: inverter IGBT
- IGBT2: brake IGBT
- Diode1: rectifier diode
- Diode2: APD inverter
- Diode3: FWD brake

Absolute Maximum Ratings

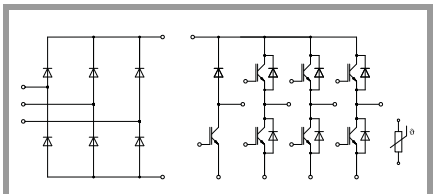
Symbol	Conditions		Values	Unit
IGBT 1				
V_{CES}	T_j = 25 °C		600	V
I_C	λ_{paste}=0.8 W/(mK)	T_s = 25 °C	58	A
	T_j = 175 °C	T_s = 70 °C	46	A
I_C	λ_{paste}=2.5 W/(mK)	T_s = 25 °C	72	A
	T_j = 175 °C	T_s = 70 °C	57	A
I_{Cnom}			50	A
I_{CRM}	I_{CRM} = 2 x I_{Cnom}		100	A
V_{GES}			-20 ... 20	V
t_{psc}	V_{CC} = 360 V $V_{GE} \leq$ 15 V $V_{CES} \leq$ 600 V	T_j = 150 °C	6	µs
T_j			-40 ... 175	°C

Absolute Maximum Ratings

Symbol	Conditions		Values	Unit
IGBT 2				
V_{CES}	T_j = 25 °C		600	V
I_C	λ_{paste}=0.8 W/(mK)	T_s = 25 °C	58	A
	T_j = 175 °C	T_s = 70 °C	46	A
I_C	λ_{paste}=2.5 W/(mK)	T_s = 25 °C	72	A
	T_j = 175 °C	T_s = 70 °C	57	A
I_{Cnom}			50	A
I_{CRM}	I_{CRM} = 2 x I_{Cnom}		100	A
V_{GES}			-20 ... 20	V
t_{psc}	V_{CC} = 360 V $V_{GE} \leq$ 15 V $V_{CES} \leq$ 600 V	T_j = 150 °C	6	µs
T_j			-40 ... 175	°C

Absolute Maximum Ratings

Symbol	Conditions		Values	Unit
Diode 1				
V_{RRM}	T_j = 25 °C		1600	V
I_F	λ_{paste}=0.8 W/(mK)	T_s = 25 °C	57	A
	T_j = 150 °C	T_s = 70 °C	43	A
I_F	λ_{paste}=2.5 W/(mK)	T_s = 25 °C	69	A
	T_j = 150 °C	T_s = 70 °C	52	A
I_{Fnom}			18	A
I_{FSM}	10 ms, sin 180°, T_j = 150 °C		350	A
i^2t	10 ms, sin 180°, T_j = 150 °C		612	A^2s
T_j			-40 ... 150	°C



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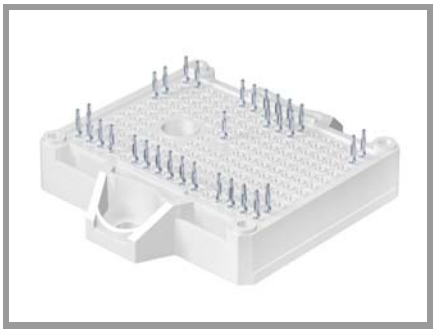

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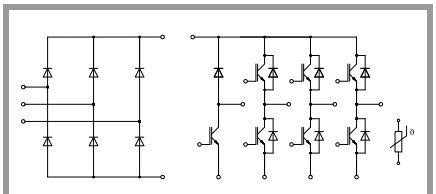
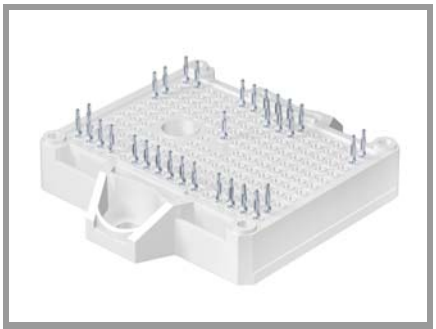


DGDL-ET

Absolute Maximum Ratings				
Symbol	**Conditions**		**Values**	**Unit**
Diode 2				
V_{RRM}	T_j = 25 °C		600	V
I_F	λ_{paste}=0.8 W/(mK)	T_s = 25 °C	52	A
	T_j = 175 °C	T_s = 70 °C	41	A
I_F	λ_{paste}=2.5 W/(mK)	T_s = 25 °C	61	A
	T_j = 175 °C	T_s = 70 °C	49	A
I_{Fnom}			50	A
I_{FRM}	I_{FRM} = 2 x I_{Fnom}		100	A
I_{FSM}	10 ms	T_j = 25 °C	345	A
	sin 180°	T_j = 150 °C	320	A
T_j			-40 ... 175	°C

Absolute Maximum Ratings				
Symbol	**Conditions**		**Values**	**Unit**
Diode 3				
V_{RRM}	T_j = 25 °C		600	V
I_F	λ_{paste}=0.8 W/(mK)	T_s = 25 °C	52	A
	T_j = 175 °C	T_s = 70 °C	41	A
I_F	λ_{paste}=2.5 W/(mK)	T_s = 25 °C	61	A
	T_j = 175 °C	T_s = 70 °C	49	A
I_{Fnom}			50	A
I_{FRM}	I_{FRM} = 2 x I_{Fnom}		100	A
I_{FSM}	10 ms	T_j = 25 °C	345	A
	sin 180°	T_j = 150 °C	320	A
T_j			-40 ... 175	°C

Absolute Maximum Ratings			
Symbol	**Conditions**	**Values**	**Unit**
Module			
$I_{t(RMS)}$	$\Delta T_{terminal}$ at PCB joint = 30 K, per pin	30	A
T_{stg}		-40 ... 125	°C
V_{isol}	AC, sinusoidal, t = 1 min	2500	V



SEMITOP®E2

3-phase bridge rectifer + brake chopper + 3-phase bridge inverter

Engineering Sample

SK50DGDL066ETE2

Target Data

Features*

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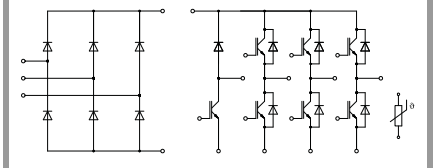
- Integrated NTC temperature sensor
- UL recognized file no. E 63 532

Typical Applications

- Motor drives
- Air conditioning
- Auxiliary Inverters

Remarks

- IGBT1: inverter IGBT
- IGBT2: brake IGBT
- Diode1: rectifier diode
- Diode2: APD inverter
- Diode3: FWD brake



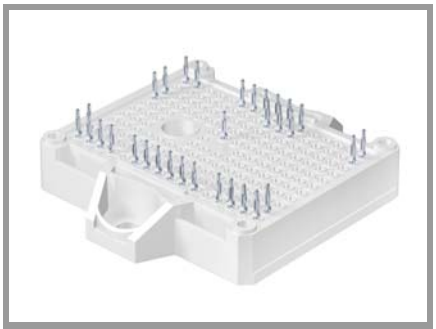
DGDL-ET

Characteristics

Symbol	Conditions		min.	typ.	max.	Unit
IGBT 1						
$V_{CE(sat)}$	I_C = 50 A V_{GE} = 15 V chiplevel	T_j = 25 °C		1.45	1.85	V
		T_j = 150 °C		1.65	2.05	V
V_{CE0}	chiplevel	T_j = 25 °C		0.90	1.10	V
		T_j = 150 °C		0.80	1.00	V
r_{CE}	V_{GE} = 15 V chiplevel	T_j = 25 °C		11	15	mΩ
		T_j = 150 °C		17	21	mΩ
$V_{GE(th)}$	V_{GE} = V_{CE}, I_C = 0.8 mA		5	5.8	6.5	V
I_{CES}	V_{GE} = 0 V, V_{CE} = 600 V, T_j = 25 °C				0.2	mA
C_{ies}	V_{CE} = 25 V V_{GE} = 0 V	f = 1 MHz		3.14		nF
C_{oes}		f = 1 MHz		0.2		nF
C_{res}		f = 1 MHz		0.093		nF
Q_G	V_{GE} = -15V...+15V			270		nC
R_{Gint}	T_j = 25 °C			0		Ω
$t_{d(on)}$	V_{CC} = 300 V I_C = 50 A V_{GE} = +15/-15 V $R_{G\ on}$ = 8.2 Ω $R_{G\ off}$ = 8.2 Ω	T_j = 150 °C		t.b.d.		ns
t_r		T_j = 150 °C		t.b.d.		ns
E_{on}		T_j = 150 °C		0.85		mJ
$t_{d(off)}$		T_j = 150 °C		t.b.d.		ns
t_f		T_j = 150 °C		t.b.d.		ns
E_{off}		T_j = 150 °C		1.6		mJ
$R_{th(j-s)}$	per IGBT, λ_{paste}=0.8 W/(mK)			1.14		K/W
$R_{th(j-s)}$	per IGBT, λ_{paste}=2.5 W/(mK)			0.82		K/W

Characteristics

Symbol	Conditions		min.	typ.	max.	Unit
IGBT 2						
$V_{CE(sat)}$	I_C = 50 A V_{GE} = 15 V chiplevel	T_j = 25 °C		1.45	1.85	V
		T_j = 150 °C		1.65	2.05	V
V_{CE0}	chiplevel	T_j = 25 °C		0.90	1.10	V
		T_j = 150 °C		0.80	1.00	V
r_{CE}	V_{GE} = 15 V chiplevel	T_j = 25 °C		11	15	mΩ
		T_j = 150 °C		17	21	mΩ
$V_{GE(th)}$	V_{GE} = V_{CE}, I_C = 0.8 mA		5	5.8	6.5	V
I_{CES}	V_{GE} = 0 V, V_{CE} = 600 V, T_j = 25 °C				0.1	mA
C_{ies}	V_{CE} = 25 V V_{GE} = 0 V	f = 1 MHz		3.14		nF
C_{oes}		f = 1 MHz		0.2		nF
C_{res}		f = 1 MHz		0.093		nF
Q_G	V_{GE} = -15V...+15V			270		nC
R_{Gint}	T_j = 25 °C			0		Ω
$t_{d(on)}$	V_{CC} = 300 V I_C = 50 A V_{GE} = +15/-15 V $R_{G\ on}$ = 8.2 Ω $R_{G\ off}$ = 8.2 Ω	T_j = 150 °C		t.b.d.		ns
t_r		T_j = 150 °C		t.b.d.		ns
E_{on}		T_j = 150 °C		0.85		mJ
$t_{d(off)}$		T_j = 150 °C		t.b.d.		ns
t_f		T_j = 150 °C		t.b.d.		ns
E_{off}		T_j = 150 °C		1.6		mJ
$R_{th(j-s)}$	per IGBT, λ_{paste}=0.8 W/(mK)			1.14		K/W
$R_{th(j-s)}$	per IGBT, λ_{paste}=2.5 W/(mK)			0.82		K/W



SEMITOP®E2

3-phase bridge rectifer + brake chopper + 3-phase bridge inverter

Engineering Sample

SK50DGDL066ETE2

Target Data

Features*

- Low inductive design
- Press-Fit contact technology
- Rugged mounting due to integrated mounting clamps
- Heat transfer and insulation through direct copper bonded aluminium oxide ceramic (DBC)
- Trench IGBT3 technology
- Robust and soft switching CAL4F diode technology
- Integrated NTC temperature sensor
- UL recognized file no. E 63 532

Typical Applications

- Motor drives
- Air conditioning
- Auxiliary Inverters

Remarks

- IGBT1: inverter IGBT
- IGBT2: brake IGBT
- Diode1: rectifier diode
- Diode2: APD inverter
- Diode3: FWD brake

Characteristics

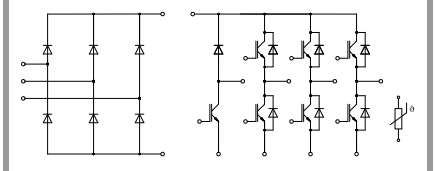
Symbol	Conditions		min.	typ.	max.	Unit
Diode 1						
V_F	I_F = 18 A	T_j = 25 °C		1.00	1.21	V
	chiplevel	T_j = 150 °C		0.90	1.10	V
V_{F0}	chiplevel	T_j = 25 °C		0.88	0.98	V
		T_j = 125 °C		0.73	0.83	V
r_F	chiplevel	T_j = 25 °C		6.7	13	mΩ
		T_j = 125 °C		9.4	15	mΩ
I_R	T_j = 145 °C, V_{RRM}				2	mA
$R_{th(j-s)}$	per Diode, λ_{paste}=0.8 W/(mK)			1.24		K/W
$R_{th(j-s)}$	per Diode, λ_{paste}=2.5 W/(mK)			0.92		K/W

Characteristics

Symbol	Conditions		min.	typ.	max.	Unit
Diode 2						
V_F	I_F = 50 A	T_j = 25 °C		1.47	1.87	V
	chiplevel	T_j = 150 °C		1.50	1.78	V
V_{F0}	chiplevel	T_j = 25 °C		0.99	1.10	V
		T_j = 150 °C		0.80	0.89	V
r_F	chiplevel	T_j = 25 °C		9.6	15	mΩ
		T_j = 150 °C		14	18	mΩ
I_{RRM}	I_F = 50 A	T_j = 150 °C		t.b.d.		A
Q_{rr}	V_{GE} = -15 V	T_j = 150 °C		t.b.d.		µC
E_{rr}	V_{CC} = 300 V	T_j = 150 °C		0.9		mJ
$R_{th(j-s)}$	per Diode, λ_{paste}=0.8 W/(mK)			1.66		K/W
$R_{th(j-s)}$	per Diode, λ_{paste}=2.5 W/(mK)			1.29		K/W

Characteristics

Symbol	Conditions		min.	typ.	max.	Unit
Diode 3						
V_F	I_F = 50 A	T_j = 25 °C		1.47	1.87	V
	chiplevel	T_j = 150 °C		1.50	1.78	V
V_{F0}	chiplevel	T_j = 25 °C		0.99	1.10	V
		T_j = 150 °C		0.80	0.89	V
r_F	chiplevel	T_j = 25 °C		9.6	15	mΩ
		T_j = 150 °C		14	18	mΩ
I_{RRM}	I_F = 50 A	T_j = 150 °C		t.b.d.		A
Q_{rr}	V_{GE} = -15 V	T_j = 150 °C		t.b.d.		µC
E_{rr}	V_{CC} = 300 V	T_j = 150 °C		0.9		mJ
$R_{th(j-s)}$	per Diode, λ_{paste}=0.8 W/(mK)			1.66		K/W
$R_{th(j-s)}$	per Diode, λ_{paste}=2.5 W/(mK)			1.29		K/W



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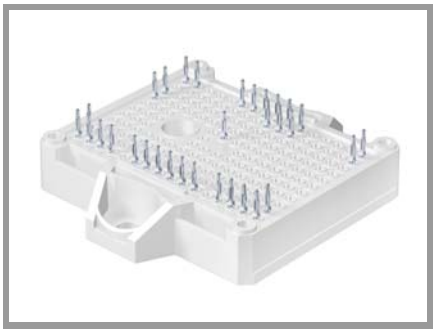

SEMITOP®E2

3-phase bridge rectifer + brake chopper + 3-phase bridge inverter

Engineering Sample

SK50DGDL066ETE2

Target Data

Features*

- Low inductive design
- Press-Fit contact technology
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- Heat transfer and insulation through direct copper bonded aluminium oxide ceramic (DBC)
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Typical Applications

- Motor drives
- Air conditioning
- Auxiliary Inverters

Remarks

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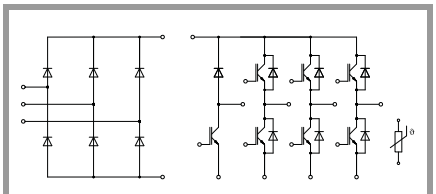
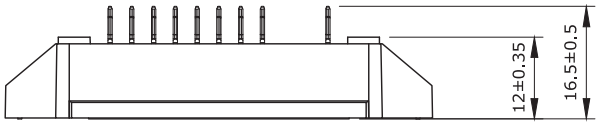
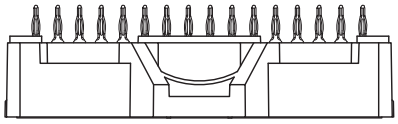


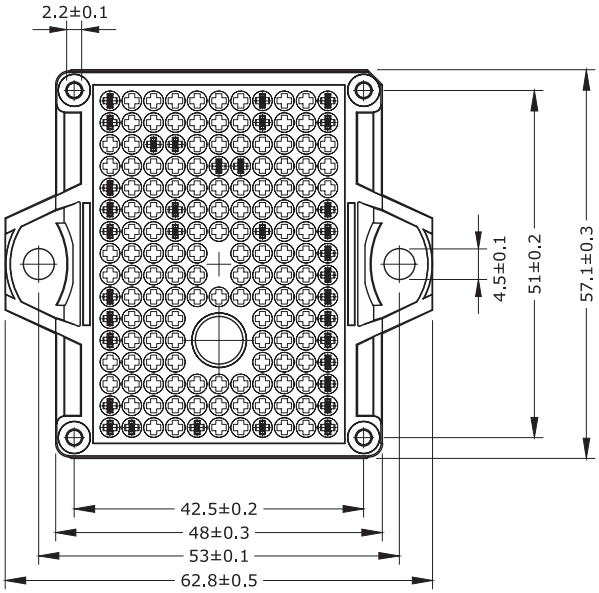
DGDL-ET

Characteristics					
Symbol	**Conditions**	**min.**	**typ.**	**max.**	**Unit**
Module					
M_s	to heatsink	1.6		2.3	Nm
w	weight		35		g

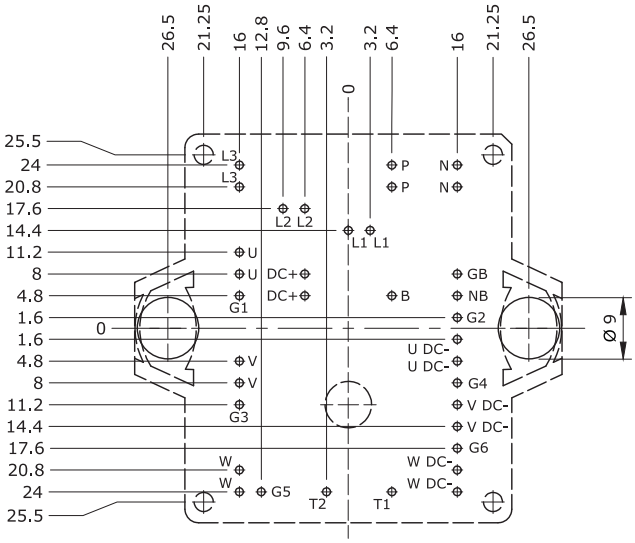
Characteristics					
Symbol	**Conditions**	**min.**	**typ.**	**max.**	**Unit**
Temperature Sensor					
R_{100}	T_r = 100 °C		493 ± 5%		Ω
$B_{100/125}$	$R_{(T)}=R_{100}\exp[B_{100/125}(1/T-1/T_{100})]$; T[K];		3550 ±2%		K







- Pin-Grid 3.2 mm
- Tolerance of PCB hole pattern ⌖ 0.025
- Diameters of drill ∅ 1.15mm
- Copper thickness in hole 25 - 50 µm
- Hole specification for contacts: refer to SEMITOP E1, E2 mounting instructions



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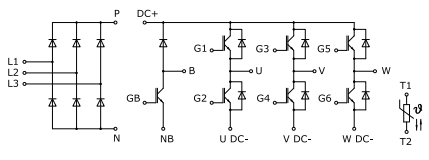

DGDL-ET

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, chapter IX.

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